

Silicon NPN Power Transistors

2SD799

DESCRIPTION

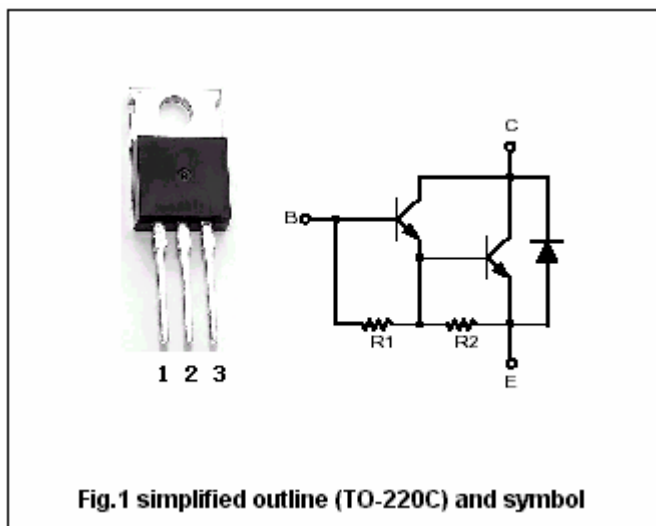
- With TO-220 package
- High DC current gain
- DARLINGTON

APPLICATIONS

- Igniter applications
- High voltage switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	600	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
I _B	Base current		1	A
P _C	Collector power dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.04A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.04A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =600V; I _E =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			3.0	mA
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =2V	600			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =2V	100			
V _{ECF}	Diode forward voltage	I _E =4A; I _B =0			3.0	V
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =50V		35		pF

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PACKAGE OUTLINE

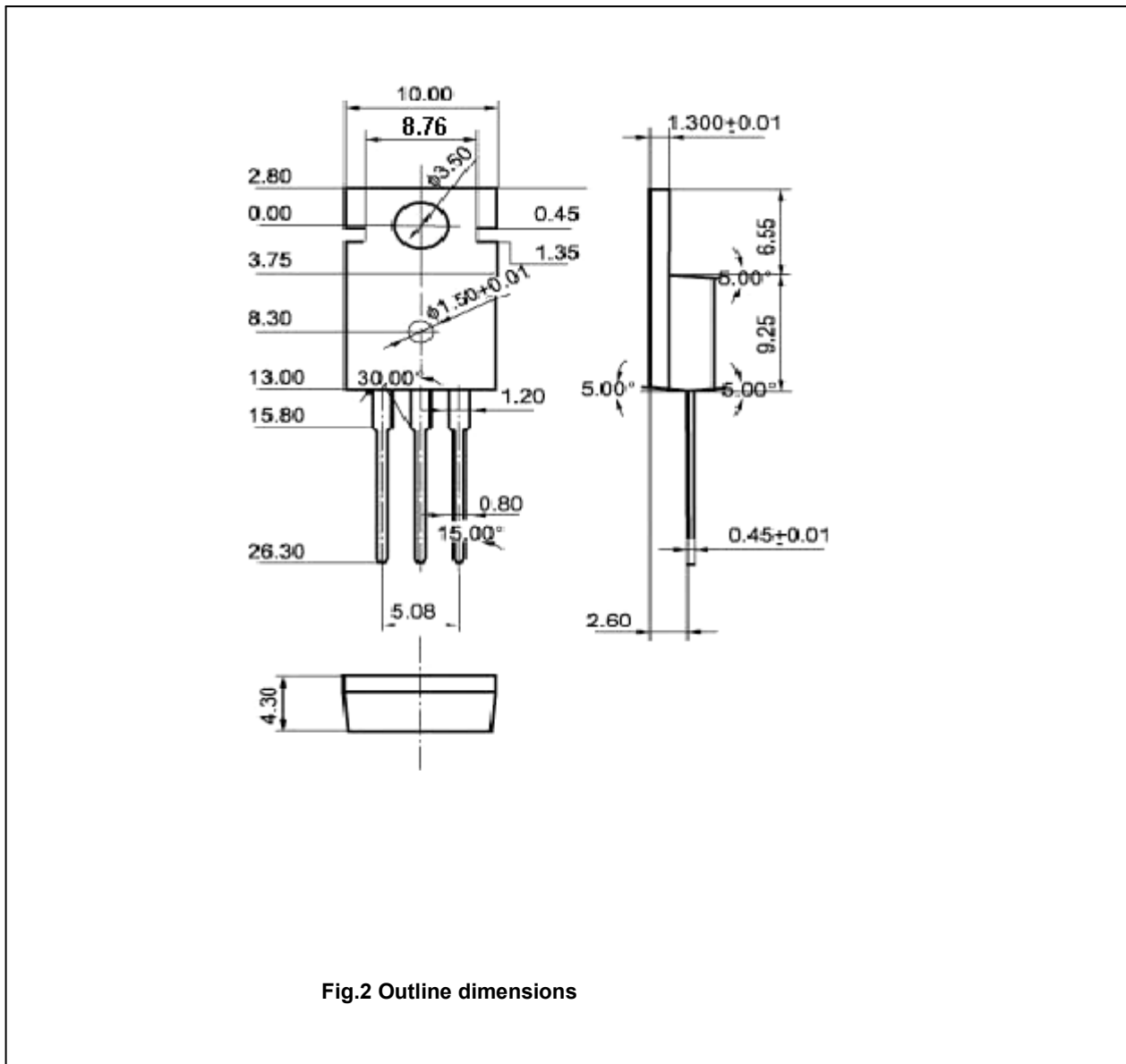


Fig.2 Outline dimensions